

Schottky Rectifier, 3.0 A


SMC


FEATURES

- 125 °C T_J operation ($V_R < 5$ V)
- Optimized for OR-ing applications
- Ultra low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Lead (Pb)-free ("PbF" suffix)
- Designed and qualified for industrial level


RoHS*
COMPLIANT

PRODUCT SUMMARY

$I_{F(AV)}$	3.0 A
V_R	15 V
I_{RM}	50 mA at 100 °C

DESCRIPTION

The 30BQ015PbF surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. The proprietary barrier technology allows for reliable operation up to 125 °C junction temperature. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Rectangular waveform	3.0	A
V_{RRM}		15	V
I_{FSM}	$t_p = 5 \mu s$ sine	650	A
V_F	1.0 Apk, $T_J = 75$ °C	0.30	V
T_J	Range	- 55 to 125	°C

VOLTAGE RATINGS

PARAMETER	SYMBOL	30BQ015PbF	UNITS
Maximum DC reverse voltage	V_R	15	V
Maximum working peak reverse voltage	V_{RWM}	25	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	50 % duty cycle at $T_L = 83$ °C, rectangular waveform	3.0	A
		50 % duty cycle at $T_L = 78$ °C, rectangular waveform	4.0	
Maximum peak one cycle non-repetitive surge current	I_{FSM}	5 μs sine or 3 μs rect. pulse	650	
		10 ms sine or 6 ms rect. pulse	75	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25$ °C, $I_{AS} = 0.5$ A, $L = 12$ mH	1.5	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum $V_A = 1.5 \times V_R$ typical	0.5	A

* Pb containing terminations are not RoHS compliant, exemptions may apply

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V _{FM} ⁽¹⁾	3 A	T _J = 25 °C	0.35	V
		6 A		0.40	
		3 A	T _J = 75 °C	0.30	
		6 A		0.35	
Maximum reverse leakage current	I _{RM} ⁽¹⁾	T _J = 25 °C	V _R = Rated V _R	4	mA
		T _J = 100 °C		50	
Maximum junction capacitance	C _T	V _R = 5 V _{DC} (test signal range 100 kHz to 1 MHz) 25 °C		1120	pF
Typical series inductance	L _S	Measured lead to lead 5 mm from package body		3.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/μs

Note(1) Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction temperature range	T _J ⁽¹⁾		- 55 to 125	°C
Maximum storage temperature range	T _{Stg}		- 55 to 150	
Maximum thermal resistance, junction to lead	R _{thJL} ⁽²⁾	DC operation	12	°C/W
Maximum thermal resistance, junction to ambient	R _{thJA}		46	
Approximate weight			0.24	g
			0.008	oz.
Marking device		Case style SMC (similar to DO-214AB)	V3C	

Notes(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

(2) Mounted 1" square PCB

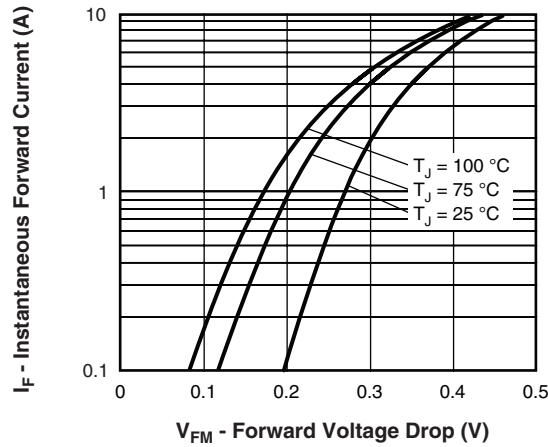


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)

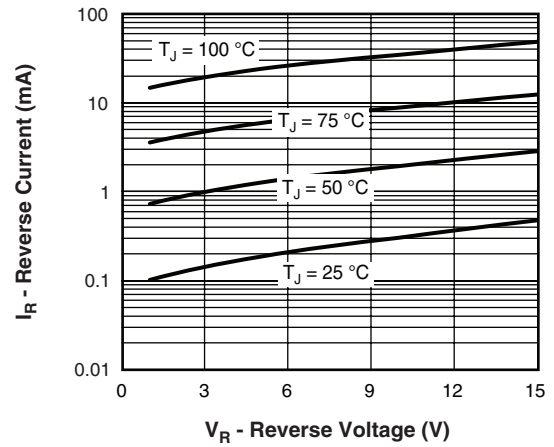


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage (Per Leg)

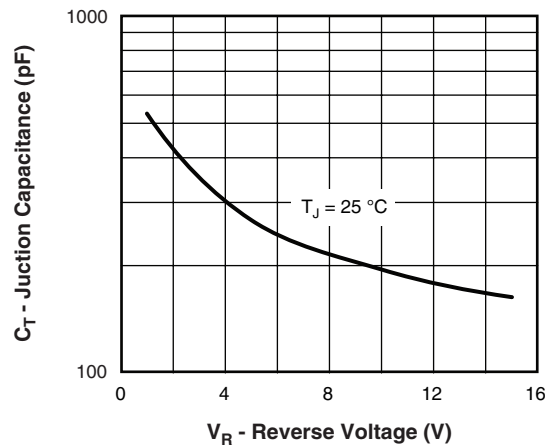


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

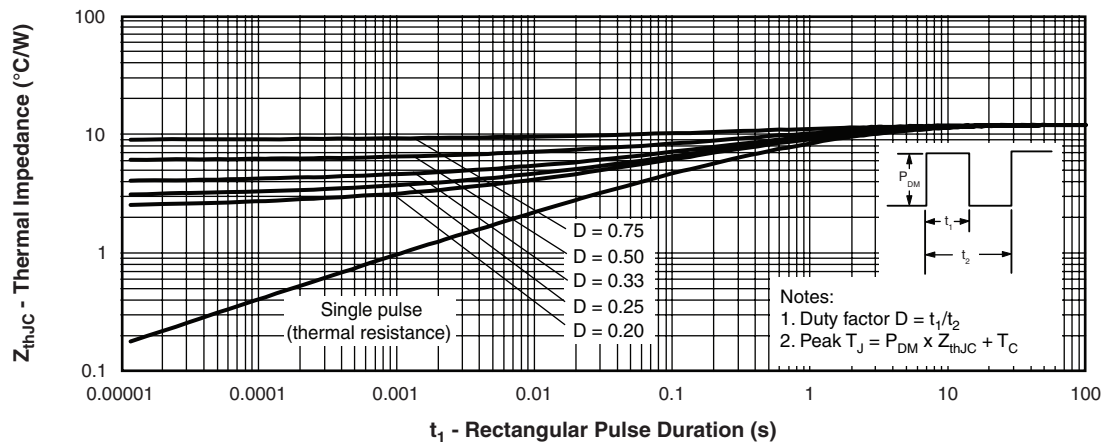


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

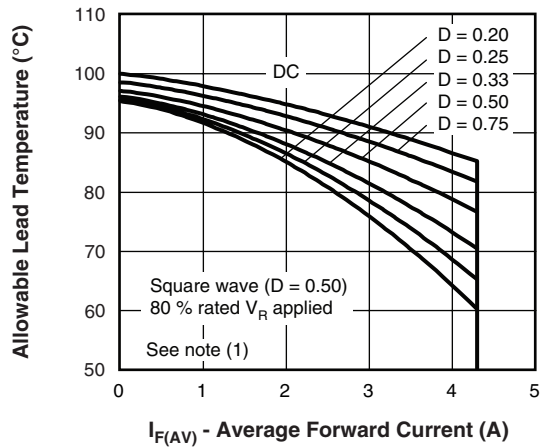


Fig. 5 - Maximum Average Forward Current vs. Allowable Lead Temperature

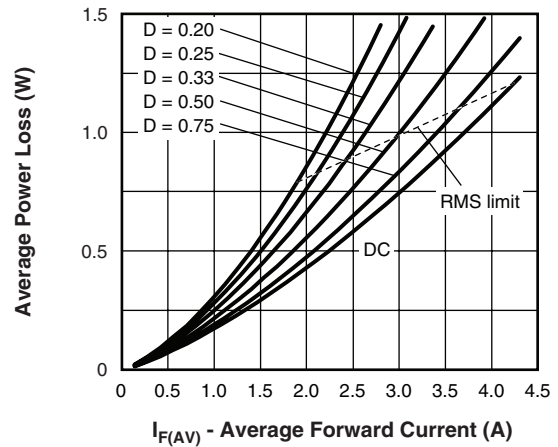


Fig. 6 - Maximum Average Forward Dissipation vs. Average Forward Current

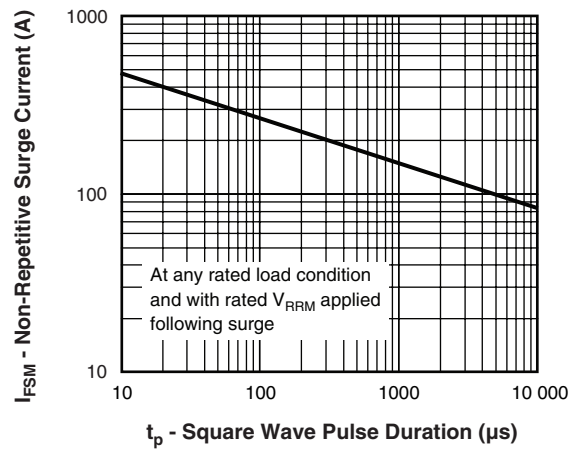


Fig. 7 - Maximum Peak Surge Forward Current vs. Pulse Duration

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R

**ORDERING INFORMATION TABLE**

Device code	30	B	Q	015	TR	PbF
	①	②	③	④	⑤	⑥
	1	-	Current rating			
	2	-	B = Single lead diode			
	3	-	Q = Schottky "Q" series			
	4	-	Voltage rating (015 = 15 V)			
	5	-	• None = Box (1000 pieces) • TR = Tape and reel (3000 pieces)			
	6	-	• None = Standard production • PbF = Lead (Pb)-free			

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95023
Part marking information	http://www.vishay.com/doc?95029
Packaging information	http://www.vishay.com/doc?95034



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